

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP60T15G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

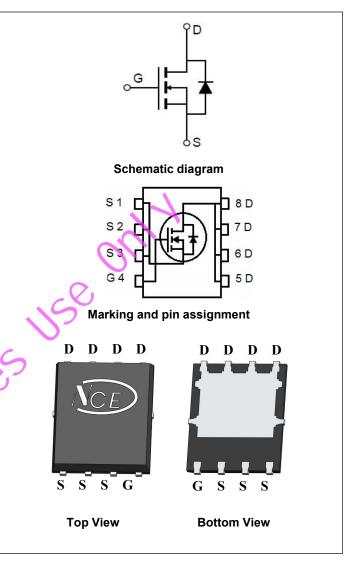
General Features

- V_{DS} =60V, I_{D} =150A $R_{DS(ON)}$ < 3.3mΩ @ V_{GS} =10V (Typ:2.8mΩ)
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P60T15G	NCEP60T15G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	150	А
Drain Current-Continuous(T _C =100 °C)	I _D (100°C)	106	Α
Pulsed Drain Current	I _{DM}	600	Α
Maximum Power Dissipation	P _D	200	W
Derating factor		1.6	W/℃
Single pulse avalanche energy (Note 1)	Eas	819	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	℃



NCEP60T15G

Thermal Characteristic

Thermal Resistance.Junction-to-Case	Rejc	0.625	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			I.	1		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics			1			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	15	2.8	3.3	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	50	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{lss}	V 20V/V 00V	-	4500	-	PF
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	965	-	PF
Reverse Transfer Capacitance	Crss	r=1.0MHZ	-	24	-	PF
Switching Characteristics (Note 2)			•			
Turn-on Delay Time	t _{d(on)}	5	-	6	-	nS
Turn-on Rise Time	t _r	V _{DD} =30V,I _D =20A	-	11	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	-	23	-	nS
Turn-Off Fall Time	t _f		-	3	-	nS
Total Gate Charge	Qg	\/ 00\/ L 00A	-	70	-	nC
Gate-Source Charge	ource Charge V _{DS} =30V,I _D =20A,		-	19	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	15.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =150A	-		1.2	V
Diode Forward Current	Is		-	-	150	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	50		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	66		nC

Notes:

^{1.} EAS condition : Tj=25 $^{\circ}\!\mathrm{C}$,V_DD=30V,V_G=10V,L=0.5mH,Rg=25 Ω

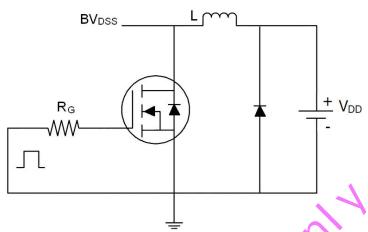
^{2.} Guaranteed by design, not subject to production

^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating..

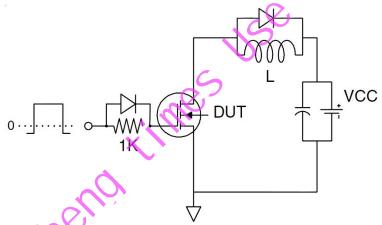


Test Circuit

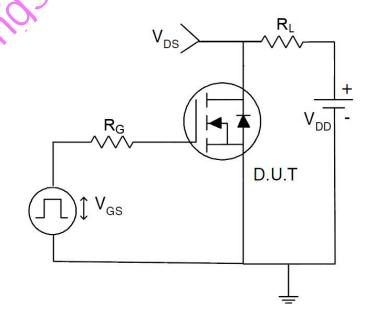
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

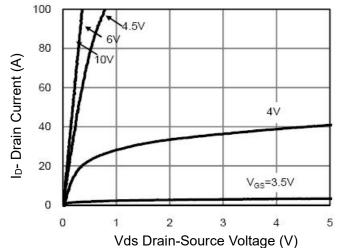


Figure 1 Output Characteristics

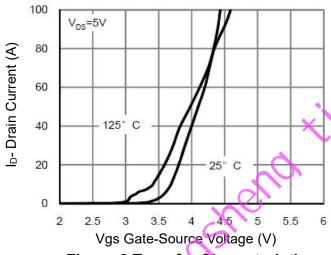


Figure 2 Transfer Characteristics

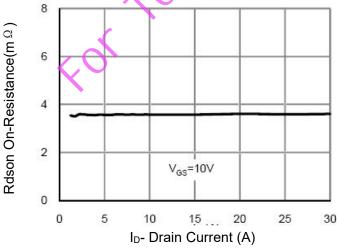


Figure 3 Rdson- Drain Current

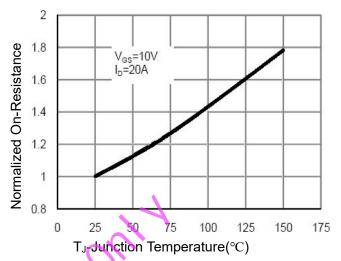


Figure 4 Rdson-Junction Temperature

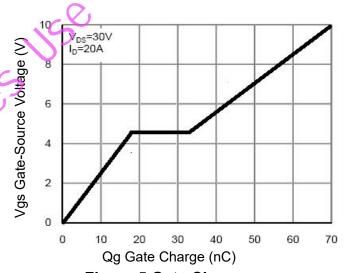


Figure 5 Gate Charge

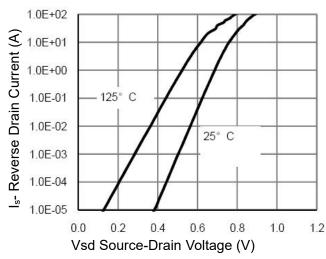


Figure 6 Source- Drain Diode Forward



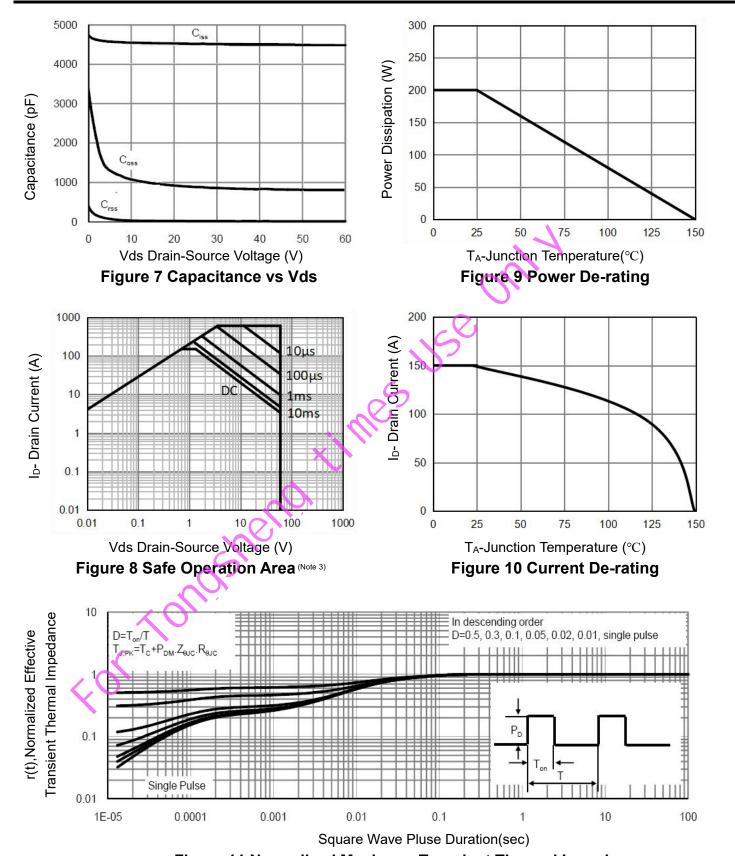
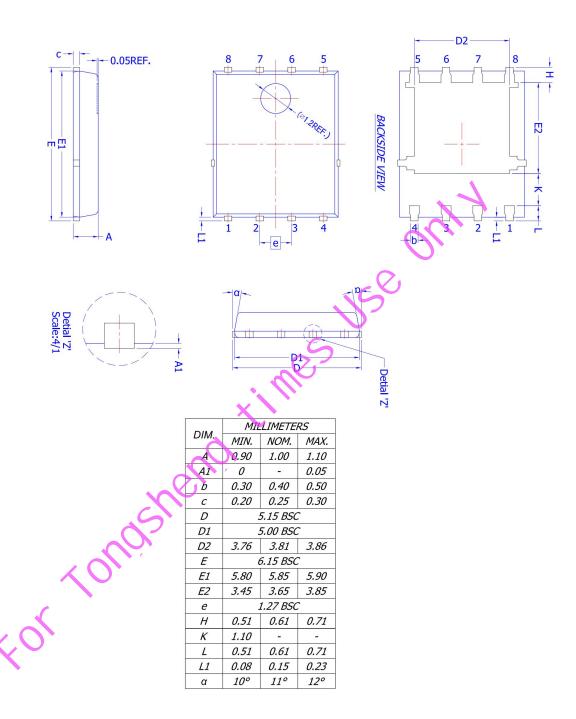


Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



Note:

- 1. All Dimension Are In mm;
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
 Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic. Body Exclusive Of Mold Flash, Tie Bar, Tie Bar Burrs Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.



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